

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

## 2SC3671

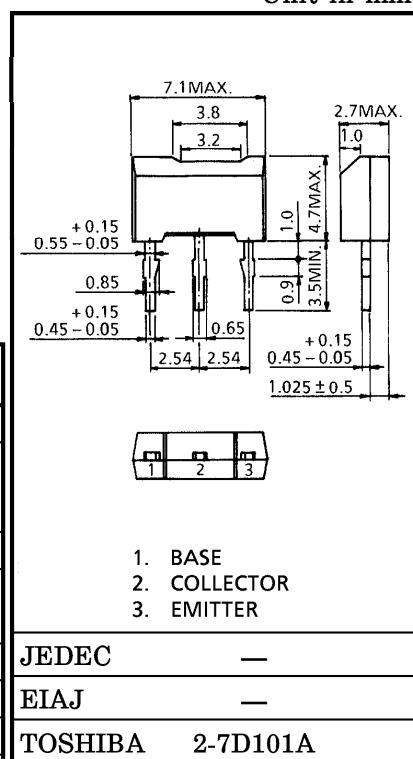
STROBE FLASH APPLICATIONS

MEDIUM POWER AMPLIFIER APPLICATIONS

- High DC Current Gain and Excellent  $h_{FE}$  Linearity
  - :  $h_{FE}(1) = 140 \sim 450$
  - :  $h_{FE}(2) = 70$  (Min.)
- Low Saturation Voltage :  $V_{CE(sat)} = 1.0V$  (Max.)

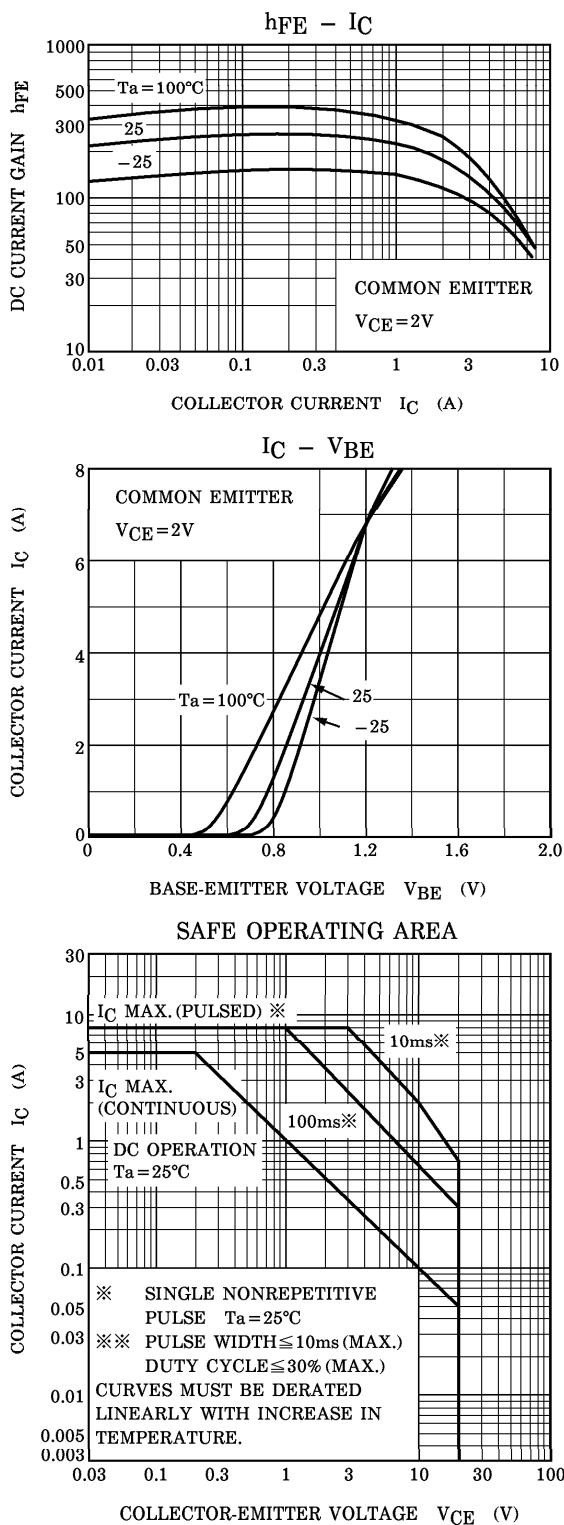
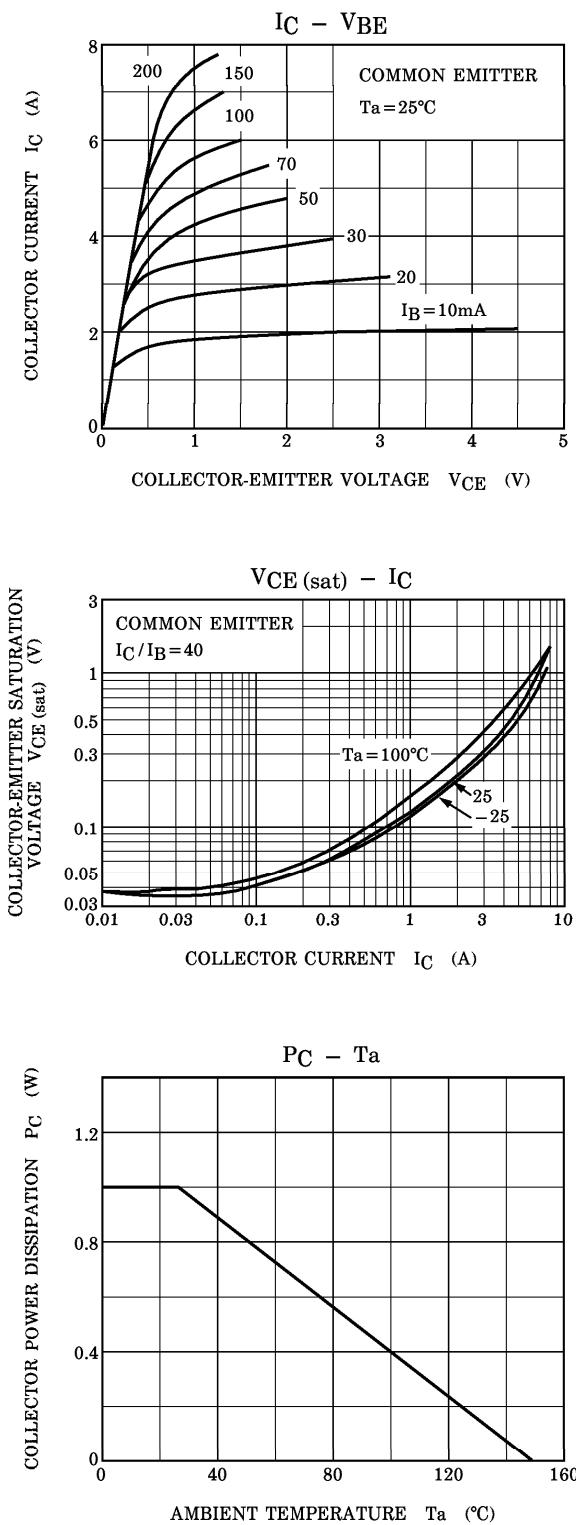
MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CBO}$	50	V
Collector-Emitter Voltage		$V_{CES}$	40	V
		$V_{CEO}$	20	
Emitter-Base Voltage		$V_{EBO}$	8	V
Collector Current	DC	$I_C$	5	A
	Pulse (Note 1)	$I_{CP}$	8	
Base Current		$I_B$	0.5	A
Collector Power Dissipation		$P_C$	1000	mW
Junction Temperature		$T_j$	150	°C
Storage Temperature Range		$T_{stg}$	$-55 \sim 150$	°C

Note 1 : Pulse Width  $\leq 10ms$ , Duty Cycle  $\leq 30\%$ ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 40V, I_E = 0$	—	—	100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 8V, I_C = 0$	—	—	100	nA
Collector-Emitter Breakdown Voltage	$V_{CEO}$	$I_C = 10mA, I_B = 0$	20	—	—	V
Emitter-Base Breakdown Voltage	$V_{EBO}$	$I_E = 1mA, I_C = 0$	8	—	—	V
DC Current Gain	$h_{FE}(1)$ (Note 2)	$V_{CE} = 2V, I_C = 0.5A$	140	—	450	
	$h_{FE}(2)$	$V_{CE} = 2V, I_C = 4A$	70	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 0.1A$	—	—	1.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 2V, I_C = 4A$	—	—	1.5	V
Transition Frequency	$f_T$	$V_{CE} = 2V, I_C = 0.5A$	—	100	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	40	—	pF

Note 2 :  $h_{FE}(1)$  Classification A : 140~240, B : 200~330, C : 300~450



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